2SA1952

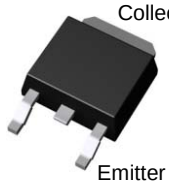
PNP -5A -60V Middle Power Transistor

Datasheet

Parameter	Value
V_{CEO}	−60V
I_C	−5A

●Outline

CPT3

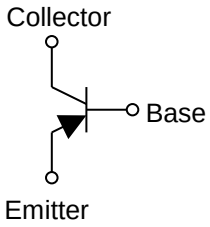


2SA1952
(SC-63)
<SOT-428>

●Features

1) Suitable for Middle Power Driver
2) Complementary NPN Types : 2SC5103
3) Low $V_{CE(sat)}$
   $V_{CE(sat)}$= −0.3V(Max.) (I_C/I_B= −3A/ −0.15A)
   $V_{CE(sat)}$= −0.5V(Max.) (I_C/I_B= −4A / −0.2A)
4) Lead Free/RoHS Compliant.

●Inner circuit



●Applications

Motor driver , LED driver
Power supply

●Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SA1952	CPT3	6595	TL	330	16	2,500	A1952

●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Values	Unit
Collector-base voltage		V_{CBO}	−100	V
Collector-emitter voltage		V_{CEO}	−60	V
Emitter-base voltage		V_{EBO}	−5	V
Collector current	DC	I_C	−5	A
	Pulsed	I_{CP}	−10	A
Power dissipation		P_D *1	1	W
		P_D *2	10	W
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	−55 to +150	°C

*1 Mounted on a substrate
*2 Tc=25°C

●Electrical characteristics (Ta = 25°C)

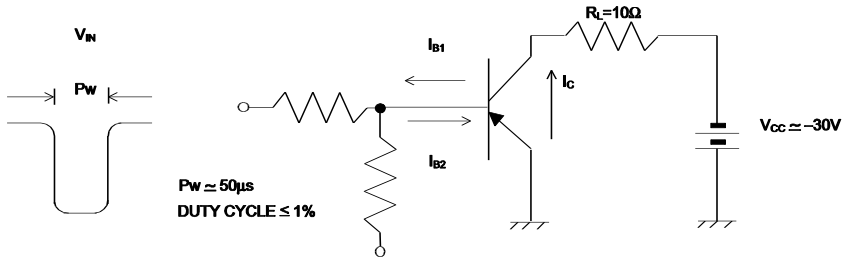
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector-emitter breakdown voltage	BV_{CEO}	I_C = –1mA	–60	-	-	V
Collector-base breakdown voltage	BV_{CBO}	I_C = –50μA	–100	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I_E = –50μA	–5	-	-	V
Collector cut-off current	I_{CBO}	V_{CB} = –100V	-	-	–10	μA
Emitter cut-off current	I_{EBO}	V_{EB} = –5V	-	-	–10	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$ *1	I_C = –3A, I_B = –0.15A	-	-	–0.3	V
		I_C = –4A, I_B = –0.2A	-	-	–0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$ *1	I_C = –3A, I_B = –0.15A	-	-	–1.2	V
		I_C = –4A, I_B = –0.2A	-	-	–1.5	V
DC current gain	h_{FE} 1*1	V_{CE} = –2V, I_C = –1A	120	-	270	-
	h_{FE} 2*1	V_{CE} = –2V, I_C = –3A	40	-	-	-
Transition frequency	f_T *1	V_{CE} = –10V, I_E = 0.5A f=30MHz	-	80	-	MHz
Output capacitance	C_{ob}	V_{CB} = –10V, I_E = 0A f = 1MHz	-	130	-	pF
Turn-on time	t_{on} *2	I_C= –3A I_{B1}= –0.15A I_{B2}=0.15A $V_{CC}\simeq$ –30V	-	-	0.3	μs
Storage time	t_{stg} *2		-	-	1.5	μs
Fall time	t_f *2		-	-	0.3	μs

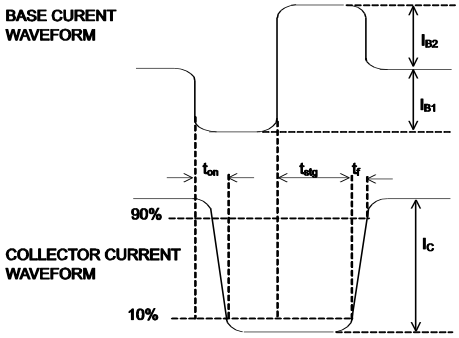
*1 Plused

*2 See switching time test circuit

●h_{FE} rank categories

Rank	Q
h_{FE}	120 to 270





●**Electrical characteristic curves**(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

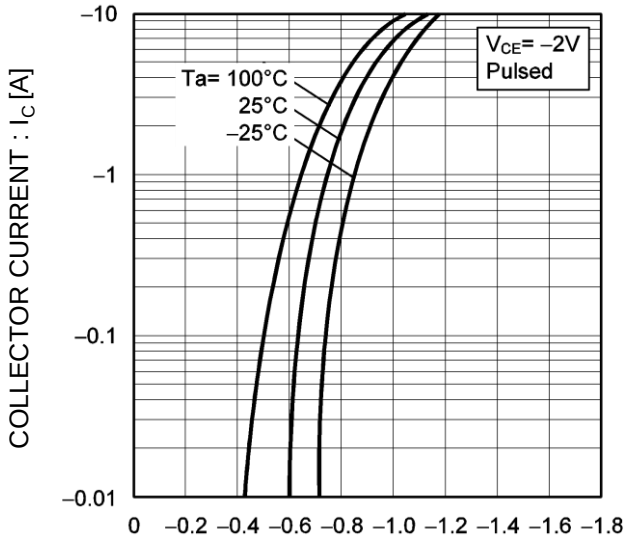


Fig.2 Typical Output Characteristics

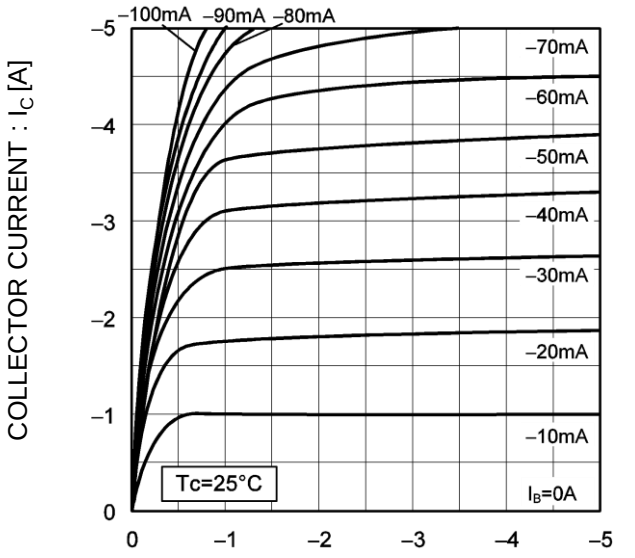


Fig.3 DC Current Gain vs. Collector Current (I)

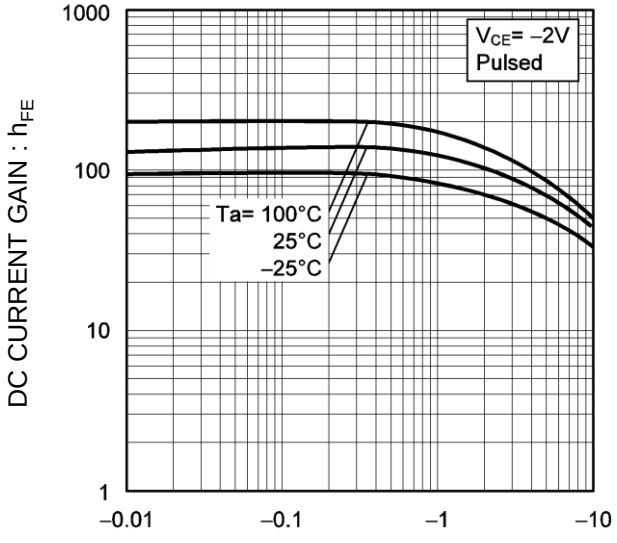
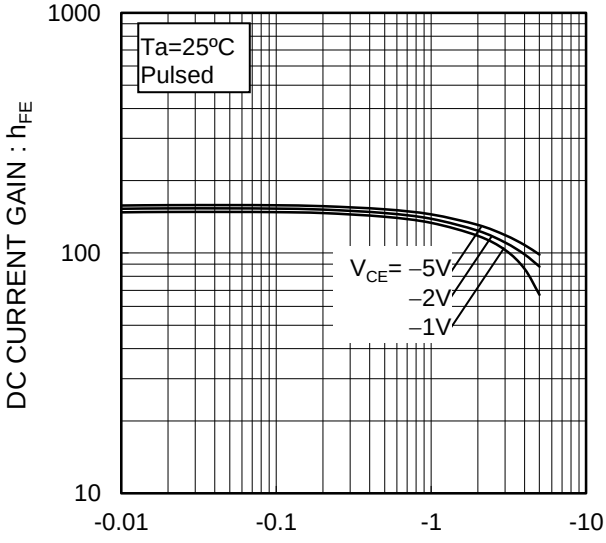


Fig.4 DC Current Gain vs. Collector Current (II)



●**Electrical characteristic curves**(Ta = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

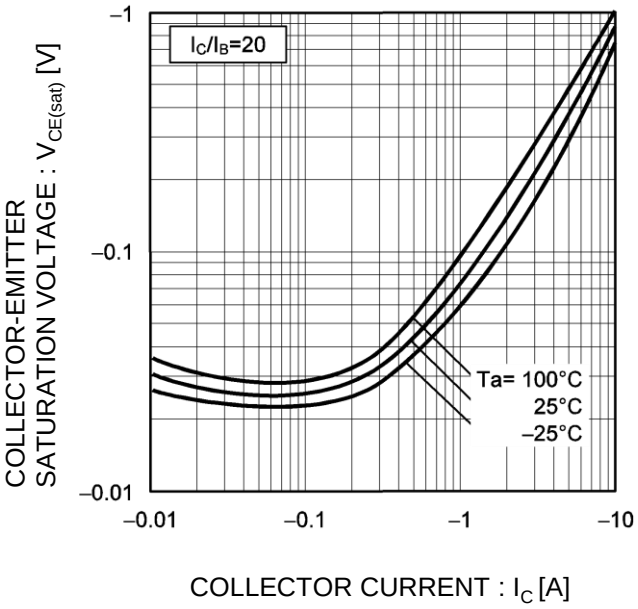


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

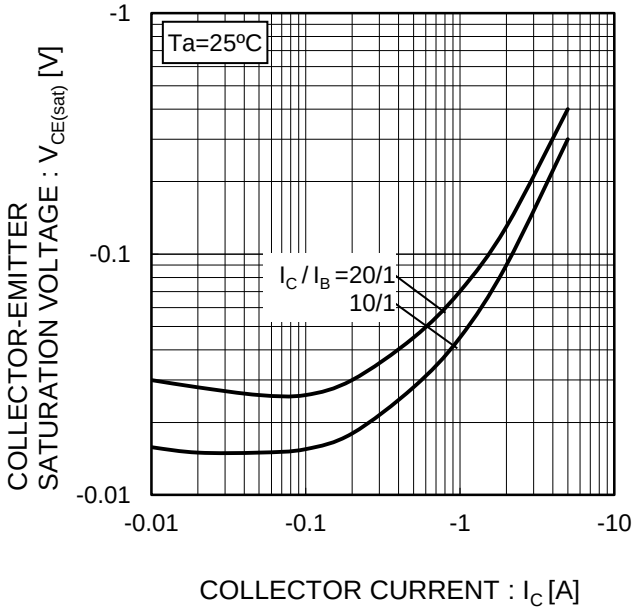


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

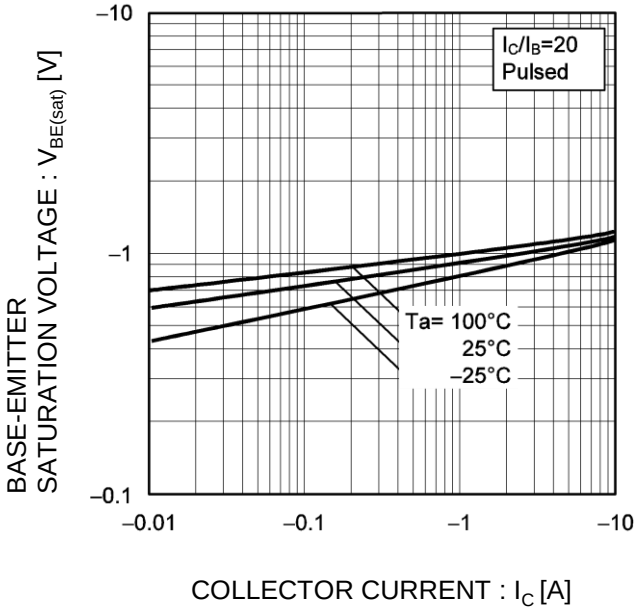
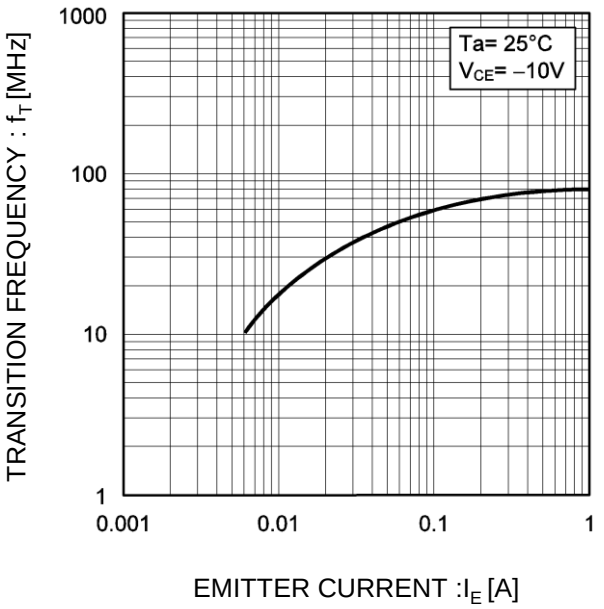


Fig.8 Gain Bandwidth Product vs. Emitter Current



●**Electrical characteristic curves**(Ta = 25°C)

Fig.9 Collector output capacitance vs. Collector-Base Voltage

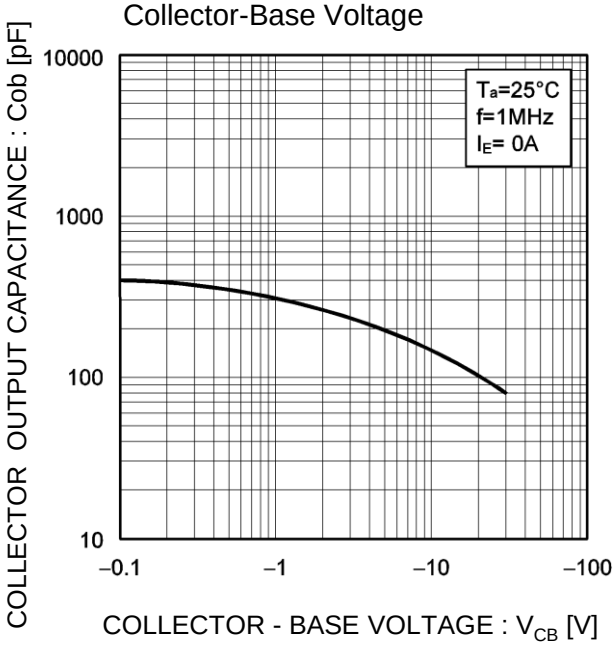
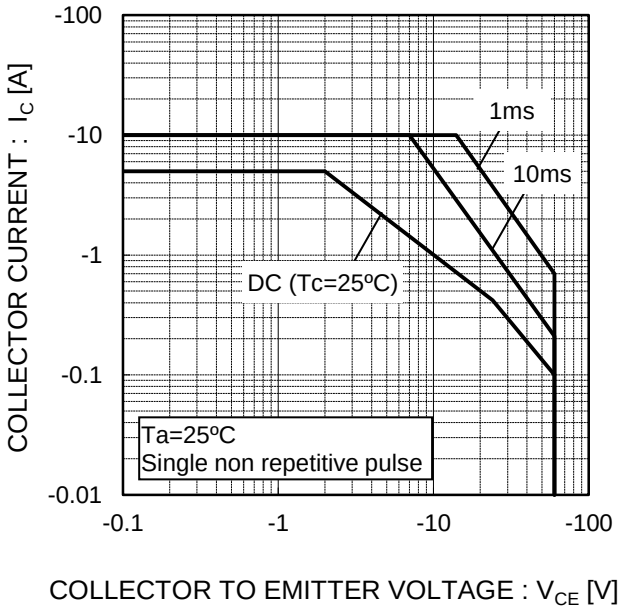
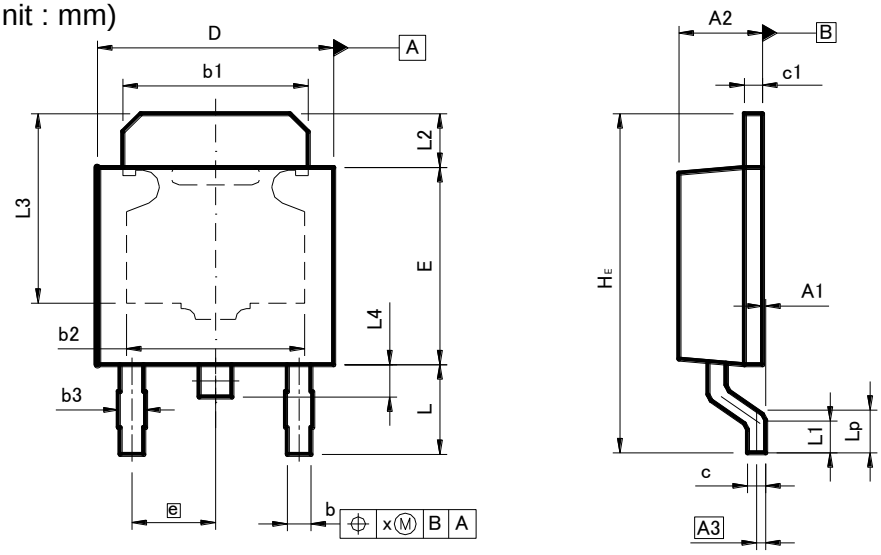


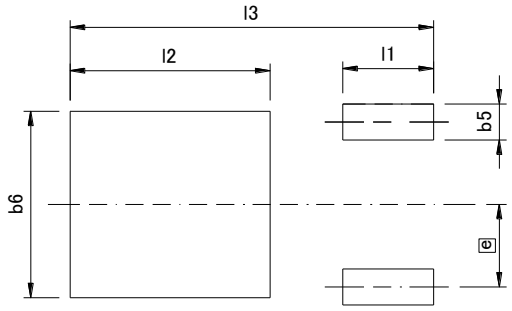
Fig.10 Safe Operating Area



●**Dimensions** (Unit : mm)

CPT3





Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A1	0.00	0.15	0.000	0.006
A2	2.20	2.50	0.087	0.098
A3	0.25		0.010	
b	0.55	0.75	0.022	0.030
b1	5.00	5.30	0.197	0.209
b2	5.00		0.197	
b3	0.75		0.030	
c	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.30	6.70	0.248	0.264
E	5.40	5.80	0.213	0.228
e	2.30		0.091	
HE	9.00	10.00	0.354	0.394
L	2.20	2.80	0.087	0.110
L1	0.80	1.40	0.031	0.055
L2	1.20	1.80	0.047	0.071
L3	5.30		0.209	
L4	0.90		0.035	
Lp	1.00	1.60	0.039	0.063
x	–	0.25	–	0.010

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b5	–	1.00	–	0.04
b6	–	5.20	–	0.205
l1	–	2.50	–	0.098
l2	–	5.50	–	0.217
l3	–	10.00	–	0.394

Dimension in mm / inches

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